





40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
-40V	51mΩ @ V _{GS} = -10V	-10.5A
-40 V	85mΩ @ V _{GS} = -4.5V	-8.4A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- · Power management functions

Features and Benefits

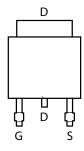
- · Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

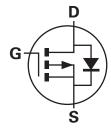
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- · Weight: 0.33 grams (approximate)



Top View



Pin Out -Top View



Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
DMP4051LK3-13	P4051L	13	16	2,500	

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



J|| = Manufacturer's Marking
P4051L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-53)





Maximum Ratings @T_A = 25°C unless otherwise specified

Char	acteristic		Symbol	Value	Unit	
Drain-Source voltage			V_{DSS}	-40	V	
Gate-Source voltage (Note 2)			V_{GS}	±20	V	
		(Note 4)	I _D	-10.5		
Continuous Drain current	$V_{GS} = 10V$	$T_A = 70^{\circ}C$ (Note 4)		-8.40	Α	
		(Note 3)		-7.2		
Pulsed Drain current V _{GS} = 10V (Note 5)		I _{DM}	-28.9	Α		
Continuous Source current (Body diode) (Note 4)		Is	-10.1	A		
Pulsed Source current (Body diode) (Note 4)		I _{SM}	-28.9	A		

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Note 3)		4.18 33.4		
Power dissipation Linear derating factor	(Note 4)	P _D	8.9 71.4	W mW/°C	
	(Note 6)		2.14 17.1		
	(Note 3)		29.9		
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	14.0	20044	
	(Note 6)	Ť	58.4	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ hetaJL}$	2.46		
Operating and storage temperature range	•	T _J , T _{STG}	-55 to 150	°C	

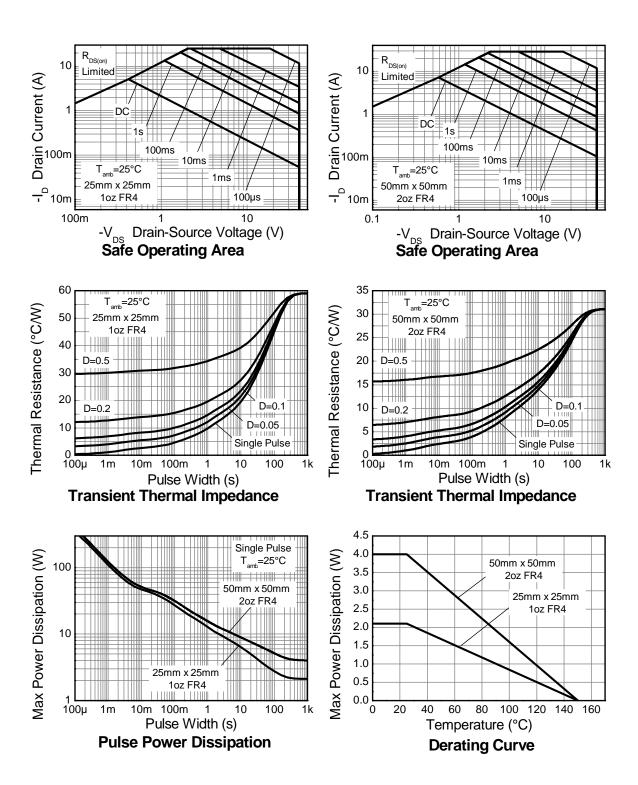
Notes:

- 2. AEC-Q101 V_{GS} maximum is $\pm 16V$.
- 3. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 4. Same as note 3, except the device is measured at $t \le 10$ sec.
- 5. Same as note 3, except the device is pulsed with D = 0.02 and pulse width $300 \, \mu s$. The pulse current is limited by the maximum junction temperature.
- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics







Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test C	ondition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-0.5	μА	V _{DS} = -40V, V _{GS} =	= 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS}	= 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	-3.0	V	I _D = -250μA, V _{DS}	= V _{GS}
Static Drain Source On Resistance (Note 9)	D		0.041	0.051	Ω	V _{GS} = -10V, I _D = -	12A
Static Drain-Source On-Resistance (Note 8)	R _{DS (ON)}	_	0.059	0.085	12	V _{GS} = -4.5V, I _D =	-8A
Forward Transconductance (Notes 8 & 9)	g fs	_	16.6	_	S	V _{DS} = -15V, I _D = -	12A
Diode Forward Voltage (Note 8)	V _{SD}	_	-0.98	-1.2	V	I _S = -12A, V _{GS} = 0)V
Reverse recovery time (Note 9)	t _{rr}		138	_	ns	I _S = -12A, di/dt= 100A/μs	
Reverse recovery charge (Note 9)	Q _{rr}	_	841	_	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		674	_	pF		
Output Capacitance	Coss	_	115	_	pF	V _{DS} = -20V, V _{GS} = 0V f= 1MHz	
Reverse Transfer Capacitance	C _{rss}		67.7	_	pF		
Total Gate Charge (Note 10)	Qg	_	7.0	_	nC	V _{GS} = -4.5V	
Total Gate Charge (Note 10)	Qg	_	14	_	nC		V _{DS} = -20V
Gate-Source Charge (Note 10)	Q _{gs}	_	2.2	_	nC	V _{GS} = -10V	I _D = -12A
Gate-Drain Charge (Note 10)	Q _{gd}	_	3.7	_	nC	1	
Turn-On Delay Time (Note 10)	t _{D(on)}		2.3	_	ns		
Turn-On Rise Time (Note 10)	tr		14.1	_	ns	V _{DD} = -20V, V _{GS} = -10V	
Turn-Off Delay Time (Note 10)	t _{D(off)}		25.1	_	ns	$I_D=-12A, R_G\cong 6.0\Omega$	
Turn-Off Fall Time (Note 10)	t _f		14.3	_	ns	1	

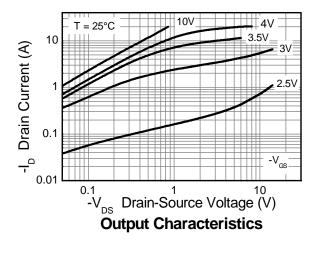
Notes:

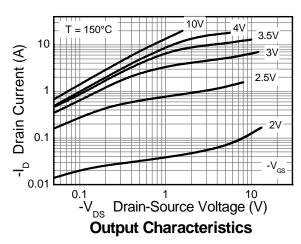
^{8.} Measured under pulsed conditions. Pulse width $\le 300 \mu s$; duty cycle $\le 2\%$ 9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures.

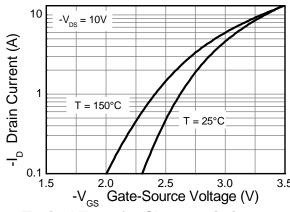


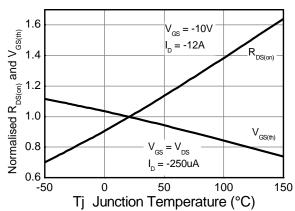


Typical Characteristics



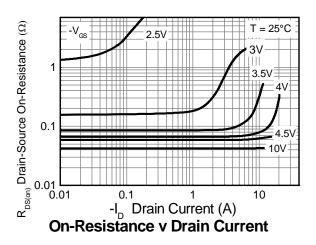


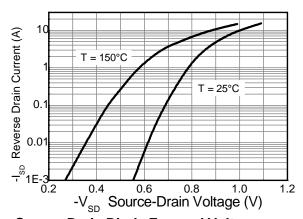




Typical Transfer Characteristics





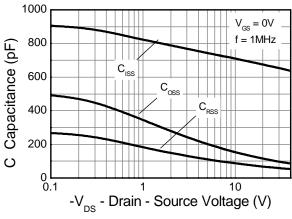


Source-Drain Diode Forward Voltage





Typical Characteristics - continued

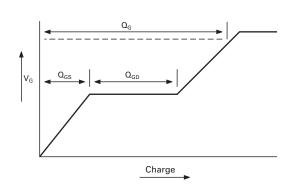


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Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge

Test Circuits



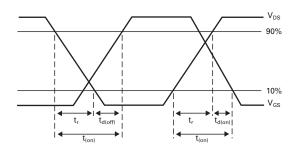
Current regulator

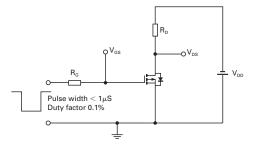
12V 0.2μF 50k Same as D.U.T

V_{os}

Basic gate charge waveform

Gate charge test circuit





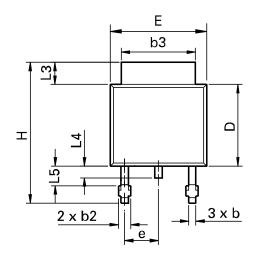
Switching time waveforms

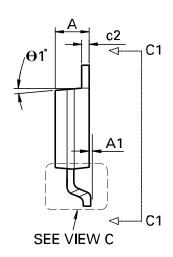
Switching time test circuit

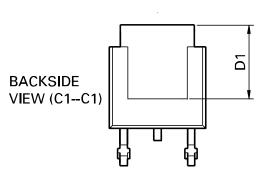


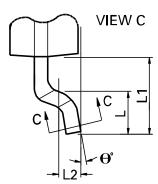


Package Outline Dimensions





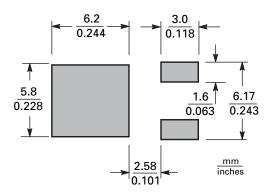




DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	9 0.090 BSC		2.29 BSC	
A 1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-



Suggested Pad Layout



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